

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

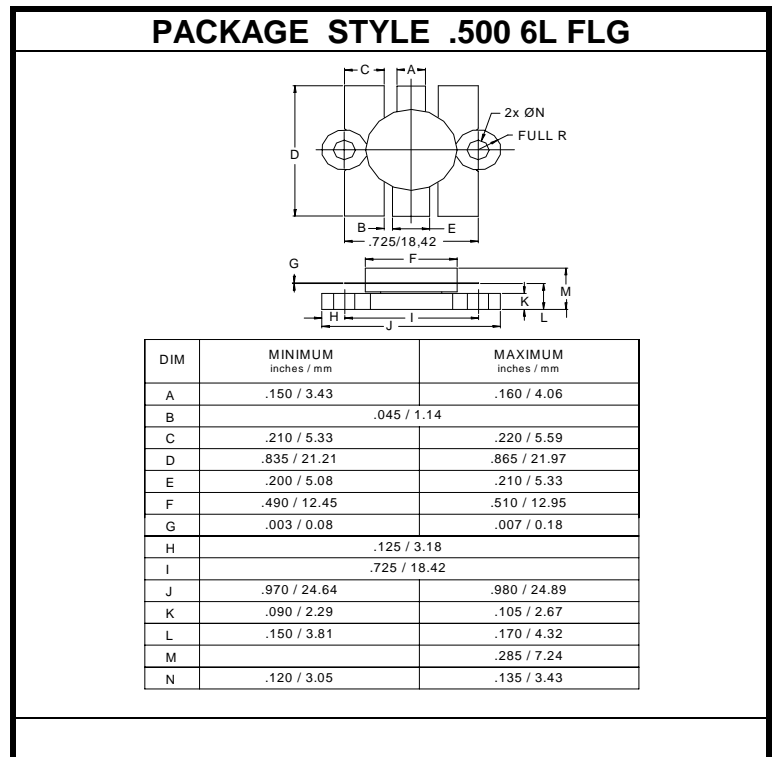
The **ASI MRF326** is Designed for High Power Class C Amplifier in, 225 to 400 MHz Military Communication Equipment.

FEATURES:

- Internal Input Matching Network
- $P_G = 8.5$ dB at 40 W/400 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.25 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	30			V
BV_{CES}	$I_C = 50$ mA	60			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CE} = 30$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 2.0$ A	10		80	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			80	pF
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 40$ W $f = 400$ MHz	8.5 60			dB %